

Power Transistors

# 2SA886

## Silicon PNP epitaxial planar type

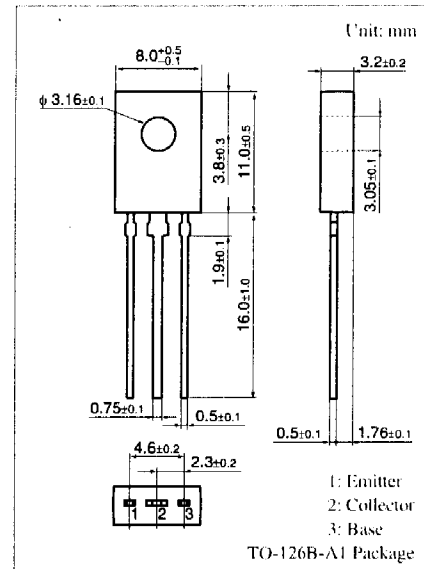
For low-frequency power amplification  
 Complementary to 2SC1847

■ Features

- Output of 4 W can be obtained by a complementary pair with 2SC1847
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-40	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-1.5	A
Peak collector current	$I_{CP}$	-3	A
Collector power dissipation	$P_C$	1.2	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -1 \text{ mA}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-40			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20 \text{ V}, I_E = 0$			-1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-10	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -5 \text{ V}, I_C = -1 \text{ A}$	80		220	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5 \text{ A}, I_B = -0.15 \text{ A}$			-1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2 \text{ A}, I_B = -0.2 \text{ A}$			-1.5	V
Transition frequency	$f_T$	$V_{CB} = -5 \text{ V}, I_E = 0.5 \text{ A}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45		pF

Rank classification

Rank	Q	R
$h_{FE1}$	80 to 160	120 to 220